

P-Ch MOSFET

General Description

The WSK100P06 is the highest performance trench P-Ch MOSFET with extreme high cell density, which provide excellent R_{DSON} and gate charge for most of the synchronous buck converter applications .

The WSK100P06 meet the RoHS and Green Product requirement, 100% EAS guaranteed with full function reliability approved.

Features

- Advanced high cell density Trench technology
- Super Low Gate Charge
- Excellent CdV/dt effect decline
- 100% EAS Guaranteed
- Green Device Available

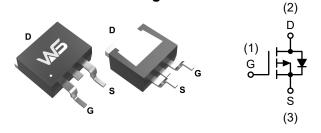
Product Summery

BV _{DSS}	R _{DSON}	I _D
-60V	5.5mΩ	-100A

Applications

• Power Management in Desktop Computer or DC/ DC Converters

TO-263-2L Pin Configuration



Symbol	Parameter	Rating	Units
V _{DS}	Drain-Source Voltage	-60	V
V _{GS}	Gate-Source Voltage	±25	V
Ι _D	Continuous Drain Current, V _{GS} @ -10V;T _C =25°C	-100	A
U	Continuous Drain Current, V _{GS} @ -10V;T _C =100°C	-58	A
ls	Diode Continuous Forward Current	-80	A
I _{AS}	Avalanche Energy, Single pulse ;L=1mH	49	A
E _{AS}	Avalanche Energy, Single pulse;;L=1mH	1200	mJ
I _{DP}	Pulse Drain Current Tested ;Tc=25°C	-264	A
P _D	Maximum Power Dissipation;T _c =25°C	250	W
	Maximum Power Dissipation;T _c =100°C	100	W
T _{STG}	Storage Temperature Range	-55 to 150	°C
TJ	Operating Junction Temperature Range	-55 to 150	°C

Thermal Data

Symbol	Parameter	Тур.	Max.	Unit
R _{θJA}	Thermal Resistance Junction-Ambient ¹		55	°C/W
R _{θJA}	Thermal Resistance Junction-Ambient 1 (t ≤10s)		20	°C/W
R _{eJC}	Thermal Resistance Junction-Case ¹		0.5	°C/W

Note : *Current limited by bond wire.

Note a : UIS tested and pulse width limited by maximum junction temperature 150 °C (initial temperature Tj=25 °C).

Absolute Maximum Ratings



P-Ch MOSFET

Electrical Characteristics (T_J=25 °C, unless otherwise noted)

Symbol	Parameter	Conditions	Min.	Тур.	Max.	Unit	
BV _{DSS}	Drain-Source Breakdown Voltage	V_{GS} =0V , I _D =-250uA	-60			V	
$\triangle BV_{DSS} / \triangle T_J$	BV _{DSS} Temperature Coefficient	Reference to 25 $^\circ\!\mathrm{C}$, I_D=-1mA		-0.018		V/℃	
Б	Static Drain-Source On-Resistance ²	V _{GS} =-10V , I _D =-20A		5.5	6.8	mΩ	
R _{DS(ON)}	Static Drain-Source On-Resistance	V _{GS} =-4.5V , I _D =-10A		9.0	12	m£2	
V _{GS(th)}	Gate Threshold Voltage		-1.3	-1.8	-2.5	V	
V _{GS(th)}	V _{GS(th)} Temperature Coefficient	$V_{GS} = V_{DS}$, $I_D = -2500A$		5.04		mV/℃	
la sa	Drain Source Leakage Current	$V_{\text{DS}}\text{=-48V}$, $V_{\text{GS}}\text{=}0\text{V}$, $T_{\text{J}}\text{=}25^\circ\!\mathbb{C}$			1		
I _{DSS}	Drain-Source Leakage Current	V_{DS} =-48V , V_{GS} =0V , TJ=55 $^\circ C$			5	uA	
I _{GSS}	Gate-Source Leakage Current	V_{GS} = $\pm25V$, V_{DS} =0V			±100	nA	
gfs	Forward Transconductance	V _{DS} =-5V , I _D =-20A		26.4		S	
Qg	Total Gate Charge (-4.5V)			136			
Q _{gs}	Gate-Source Charge	V_{DS} =-30V , V_{GS} =-4.5V , I_{D} =-20A		20		nC	
Q _{gd}	Gate-Drain Charge			33			
T _{d(on)}	Turn-On Delay Time			18			
Tr	Rise Time	V_{DD} =-15V , V_{GS} =-10V ,		20		20	
T _{d(off)}	Turn-Off Delay Time	R _G =3.3Ω, I _D =-20A		200		ns	
T _f	Fall Time			120			
C _{iss}	Input Capacitance			6095			
Coss	Output Capacitance	V _{DS} =-15V , V _{GS} =0V , f=1MHz		1080		pF	
C _{rss}	Reverse Transfer Capacitance			430			

Diode Characteristics

Symbol	Parameter	Conditions		Тур.	Max.	Unit
Is	Continuous Source Current ^{1,6}				-80	А
I _{SM}	Pulsed Source Current ^{2,6}	V _G =V _D =0V , Force Current			-160	А
V _{SD}	Diode Forward Voltage ²	V _{GS} =0V , I _S =-1A , TJ=25℃			-1.2	V
t _{rr}	Reverse Recovery Time	IF=-20A,dI/dt=100A/µs , Tյ=25℃		30		nS
Qrr	Reverse Recovery Charge	ii20Λ,αι/αι-100Λ/μ3 , 1j-20 C		20		nC

Note :

1. The data tested by surface mounted on a 1 inch² FR-4 board with 2OZ copper,t<10sec.

2.The data tested by pulsed , pulse width $\,\leq\,$ 300us , duty cycle $\,\leq\,$ 2%

3. The EAS data shows Max. rating . The test condition is V_{DD} =-25V, V_{GS} =-10V, L=0.1mH, I_{AS} =-30A

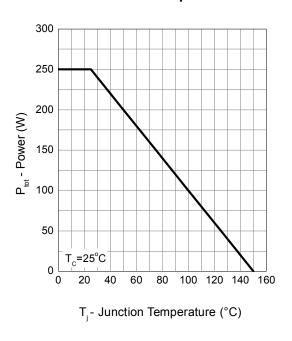
- 4.The power dissipation is limited by 150°C junction temperature
- 5. The Min. value is 100% EAS tested guarantee.

6. The data is theoretically the same as I_{D} and I_{DM} , in real applications , should be limited by total power dissipation.

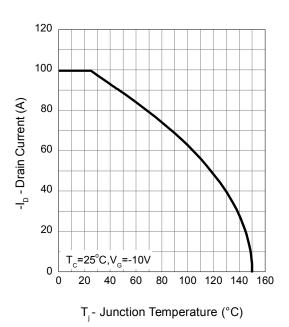


P-Ch MOSFET

Typical Characteristics



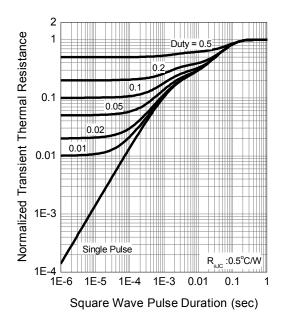
Power Dissipation



Drain Current

Safe Operation Area

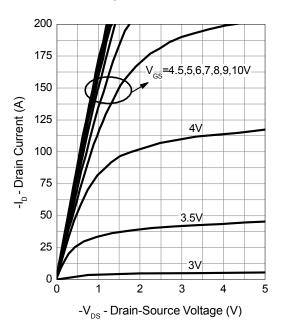
Thermal Transient Impedance



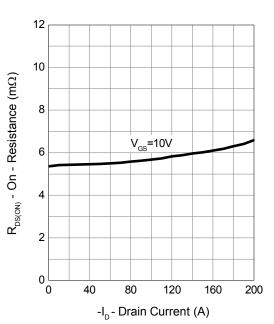


P-Ch MOSFET

Typical Characteristics

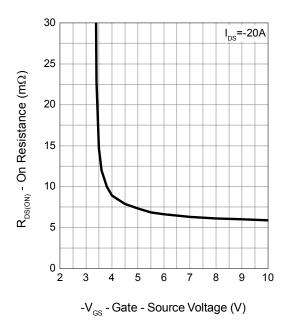


Output Characteristics

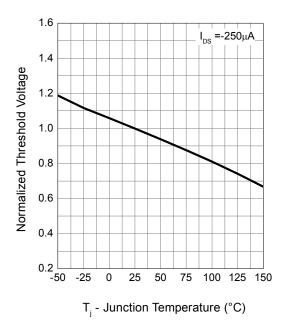


Drain-Source On Resistance

Gate-Source On Resistance



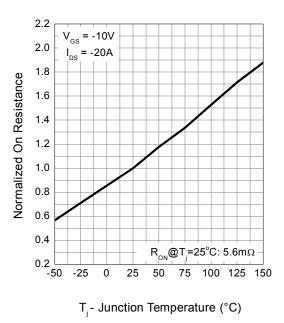
Gate Threshold Voltage





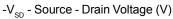
P-Ch MOSFET

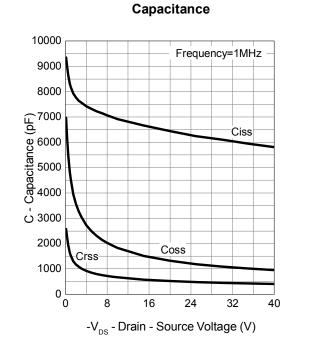
Typical Characteristics



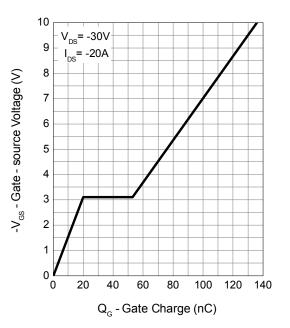
Drain-Source On Resistance

Source-Drain Diode Forward





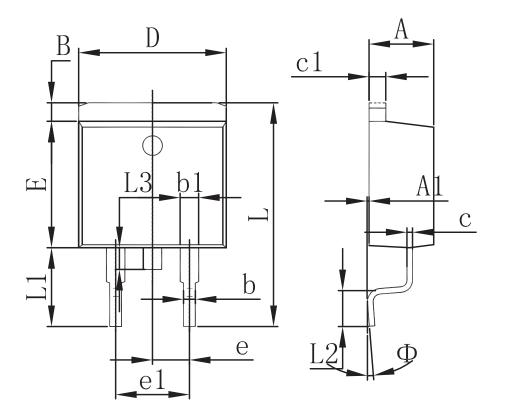
Gate Charge

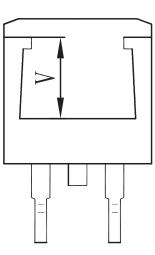




P-Ch MOSFET

Packaging information





Symbol	Dimensions In Millimeters		Dimensions In Inches		
Symbol	Min.	Max.	Min.	Max.	
A	4.470	4.670	0.176	0.184	
A1	0.000	0.150	0.000	0.006	
В	1.120	1.420	0.044	0.056	
b	0.710	0.910	0.028	0.036	
b1	1.170	1.370	0.046	0.054	
С	0.310	0.530	0.012	0.021	
c1	1.170	1.370	0.046	0.054	
D	10.010	10.310	0.394	0.406	
E	8.500	8.900	0.335	0.350	
е	2.540	2.540 TYP.		TYP.	
e1	4.980	5.180	0.196	0.204	
L	14.940	15.500	0.588	0.610	
L1	4.950	5.450	0.195	0.215	
L2	2.340	2.740	0.092	0.108	
L3	1.300	1.700	0.051	0.067	
Φ	0°	8°	0°	8°	
V	5.600 REF.		0.220REF.		



Attention

1, Any and all Winsok power products described or contained herein do not have specifications that can handle applications that require extremely high levels of reliability, such as life-support systems, aircraft's control systems, or other applications whose failure can be reasonably expected to result in serious physical and/or material damage. Consult with your Winsok power representative nearest you before using any Winsok power products described or contained herein in such applications.

2, Winsok power assumes no responsibility for equipment failures that result from using products at values that exceed, even momentarily, rated values (such as maximum ratings, operating condition ranges, or other parameters) listed in products specifications of any and all Winsok power products described or contained herein.

3, Specifications of any and all Winsok power products described or contained herein stipulate the performance, characteristics, and functions of the described products in the independent state, and are not guarantees of the performance, characteristics, and functions of the described products as mounted in the customer's products or equipment. To verify symptoms and states that cannot be evaluated in an independent device, the customer should always evaluate and test devices mounted in the customer's products or equipment.

4, Winsok power Semiconductor CO., LTD. strives to supply high-quality high-reliability products. However, any and all semiconductor products fail with some probability. It is possible that these probabilistic failures could give rise to accidents or events that could endanger human lives that could give rise to smoke or fire, or that could cause damage to other property. When designing equipment, adopt safety measures so that these kinds of accidents or events cannot occur. Such measures include but are not limited to protective circuits and error prevention circuits for safe design, redundant design, and structural design.

5, In the event that any or all Winsok power products (including technical data, services) described or contained herein are controlled under any of applicable local export control laws and regulations, such products must not be exported without obtaining the export license from the authorities concerned in accordance with the above law.

6, No part of this publication may be reproduced or transmitted in any form or by any means, electronic or mechanical, including photocopying and recording, or any information storage or retrieval system, or otherwise, without the prior written permission of Winsok power Semiconductor CO., LTD.

7, Information (including circuit diagrams and circuit parameters) herein is for example only; it is not guaranteed for volume production. Winsok power believes information herein is accurate and reliable, but no guarantees are made or implied regarding its use or any infringements of intellectual property rights or other rights of third parties.

8, Any and all information described or contained herein are subject to change without notice due to product/technology improvement, etc. When designing equipment, refer to the "Delivery Specification" for the Winsok power product that you Intend to use.

9, this catalog provides information as of Sep.2014. Specifications and information herein are subject to change without notice.